

Precision Monolithic Quad SPST CMOS Analog Switches

DESCRIPTION

The DG417B, DG418B, DG419B monolithic CMOS analog switches were designed to provide high performance switching of analog signals. Combining low power, low leakages, high speed, low on-resistance and small physical size, the DG417B series is ideally suited for portable and battery powered industrial and military applications requiring high performance and efficient use of board space.

To achieve high-voltage ratings and superior switching performance, the DG417B series is built on Vishay Siliconix's high voltage silicon gate (HVSG) process. Break-before-make is guaranteed for the DG419B, which is an SPDT configuration. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

The DG417B and DG418B respond to opposite control logic levels as shown in the Truth Table.

FEATURES

- ± 15 V analog signal range
- On-resistance - $R_{DS(on)}$: $15\ \Omega$
- Fast switching action - t_{ON} : 110 ns
- TTL and CMOS compatible
- 8-pin CerDIP package

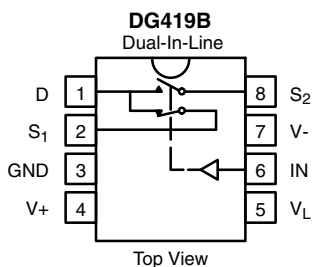
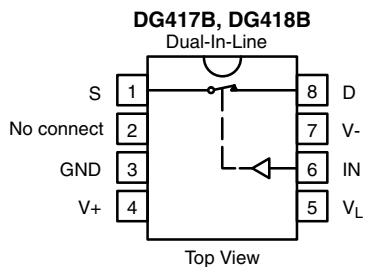
BENEFITS

- Widest dynamic ranges
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing
- Reduced board space
- Improved reliability

APPLICATIONS

- Precision test equipment
- Precision instrumentation
- Battery powered systems
- Sample-and-hold circuits
- Military radios
- Hi-Rel systems
- Guidance and control systems
- Hard disk drivers

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

LOGIC	DG417B	DG418B
0	On	Off
1	Off	On

Notes

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V

TRUTH TABLE (DG419B)

LOGIC	SW ₁	SW ₂
0	On	Off
1	Off	On

Notes

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V

**ORDERING INFORMATION**

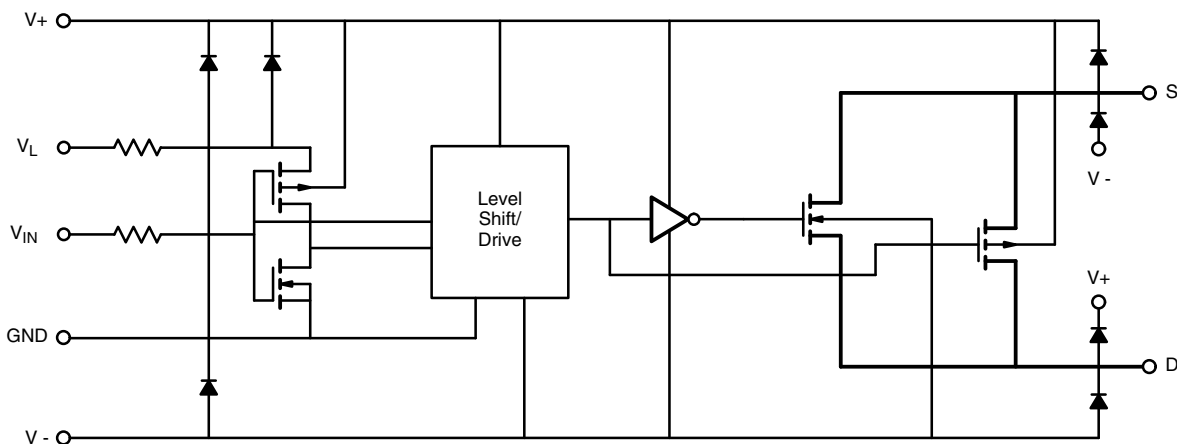
PART	CONFIGURATION	TEMP. RANGE	PACKAGE	ORDERING PART	GENERIC	DSCC NUMBER
DG417B	SPST x 1, NC	- 55 °C to 125 °C	8-pin CerDIP	9073704PA	DG417BAK/883	5962-9073704MPA
				DG417BAK	DG417BAK	-
				DG417BAK-E3	DG417BAK-E3	-
DG418B	SPST x 1, NO			9073705PA	DG418BAK/883	5962-9073705MPA
				DG418BAK	DG418BAK	-
				DG418BAK-E3	DG418BAK-E3	-
DG419B	SPDT x 1			9073706PA	DG419BAK/883	5962-9073706MPA
				DG419BAK	DG419BAK	-
				DG419BAK-E3	DG419BAK-E3	-

ABSOLUTE MAXIMUM RATINGS

PARAMETER		LIMIT	UNIT
Voltages Referenced to V-	V+	44	V
	GND	25	
V_L		(GND - 0.3) to (V+) + 0.3	
Digital inputs ^a , V_S , V_D		(V-) - 2 V to (V+) + 2 or 30 mA, whichever occurs first	
Current, (any terminal) continuous		30	mA
Current (S or D) pulsed at 1 ms, 10 % duty cycle		100	
Storage temperature		- 65 to 150	°C
Power dissipation (package) ^b	8-pin CerDIP ^c	600	mW

Notes

- a. Signals on S_X , D_X or IN_X exceeding V + or V - will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads soldered or welded to PC board.
c. Derate 8 mW/°C above 75 °C.

SCHEMATIC DIAGRAM (Typical Channel)**Fig. 1**



SPECIFICATIONS ^a									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 15 V, V ₋ = - 15 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^f		TEMP. ^b	TYP. ^c	A SUFFIX - 55 °C to 125 °C		UNIT	
						MIN. ^d	MAX. ^d		
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}			Full		- 15	15	V	
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = ± 12.5 V V ₊ = 13.5 V, V ₋ = - 13.5 V		Room	15		25	Ω	
				Full	15		34		
Switch Off Leakage Current	I _{S(off)}	V ₊ = 16.5, V ₋ = - 16.5 V V _D = ± 15.5 V, V _S = ± 15.5 V		Room	- 0.1	- 0.25	0.25	nA	
				Full	- 0.1	- 20	20		
	I _{D(off)}			Room	- 0.1	- 0.25	0.25		
				Full	- 0.1	- 20	20		
				Room	- 0.1	- 0.25	0.25		
				Full	- 0.1	- 20	20		
				Room	- 0.1	- 0.75	0.75		
				Full	- 0.1	- 60	60		
Channel On Leakage Current	I _{D(on)}	V ₊ = 16.5 V, V ₋ = - 16.5 V V _S = V _D = ± 15.5 V	DG417B	Room	- 0.4	- 0.4	0.4		
			Full	- 0.4	- 40	40			
			DG418B	Room	- 0.4	- 0.4	0.4		
			Full	- 0.4	- 40	40			
			DG419B	Room	- 0.4	- 0.75	0.75		
			Full	- 0.4	- 60	60			
Digital Control									
Input Current, V _{IN} Low	I _{IL}			Full		- 0.5	0.5	μA	
Input Current, V _{IN} High	I _{IH}			Full		- 0.5	0.5		
Dynamic Characteristics									
Turn-On Time	t _{ON}	R _L = 300 Ω, C _L = 35 pF V _S = ± 10 V, see switching time test circuit		DG417B	Room	62		89	ns
				Full	62		106		
DG418B	Room			62		89			
Full	62				106				
Turn-Off Time	t _{OFF}			DG417B	Room	53		80	
				Full	53		88		
		DG418B	Room	53		80			
		Full	53		88				
Transition Time	t _{TRANS}	R _L = 300 Ω, C _L = 35 pF V _{S1} = ± 10 V, V _{S2} = ± 10 V		DG419B	Room	60		87	
				Full	60		96		
Break-Before-Make Time Delay	t _D	R _L = 300 Ω, C _L = 35 pF V _{S1} = V _{S2} = ± 10 V		DG419B	Room	16	3		
Charge Injection	Q	C _L = 10 nF, V _{gen} = 0 V, R _{gen} = 0 Ω		Room	38			pC	
Off Isolation ^e	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz		Room	- 82			dB	
Channel-to-Channel Crosstalk ^e	X _{TALK}			DG419B	Room	- 88			
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V _S = 0 V		Room	12			pF	
Drain Off Capacitance ^e	C _{D(off)}			DG417B	Room	12			
				DG418B	Room	12			
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz, V _S = 0 V		DG417B	Room	50			
				DG418B	Room	50			
				DG419B	Room	57			



SPECIFICATIONS ^a								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = - 0 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^f	TEMP. ^b	TYP. ^c	A SUFFIX - 55 °C to 125 °C		UNIT	
					MIN. ^d	MAX. ^d		
Power Supplies								
Positive Supply Current	I ₊	V ₊ = 16.5 V, V ₋ = - 16.5 V V _{IN} = 0 V or 5 V	Room	0.001		1	μA	
			Full			5		
Negative Supply Current	I ₋		Room	- 0.001	- 1			
			Full		- 5			
Logic Supply Current	I _L		Room	0.001		1		
			Full			5		
Ground Current	I _{GND}		Room	- 0.001	- 1			
			Full		- 5			
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	V	
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = 3.8 V V ₊ = 10.8 V	Room	26		35	Ω	
			Full	26		52		
Dynamic Characteristics								
Turn-On Time	t _{ON}	R _L = 300 Ω, C _L = 35 pF V _S = 8 V, see switching time test circuit	Room	100		125	ns	
			Full	100		155		
Turn-Off Time	t _{OFF}		Room	38		66		
			Full	38		69		
Break-Before-Make Time Delay	t _D	R _L = 300 Ω, C _L = 35 pF	DG419B	Room	62	25		
Transition Time	t _{TRANS}	R _L = 300 Ω, C _L = 35 pF V _{S1} = 0 V, 8 V, V _{S2} = 8 V, 0 V	Room	95		119		
			Full	95		153		
Charge Injection	Q	C _L = 10 nF, V _{gen} = 0 V, R _{gen} = 0 Ω		Room	18		pC	
Power Supplies								
Positive Supply Current	I ₊	V ₊ = 13.2 V, V _L = 5.25 V V _{IN} = 0 V or 5 V		Room	0.001		1	μA
				Full	0.001		5	
Negative Supply Current	I ₋			Room	- 0.001	- 1 - 5		
Logic Supply Current	I _L			Room	0.001		1 5	
Ground Current	I _{GND}			Room	- 0.001	- 1 - 5		

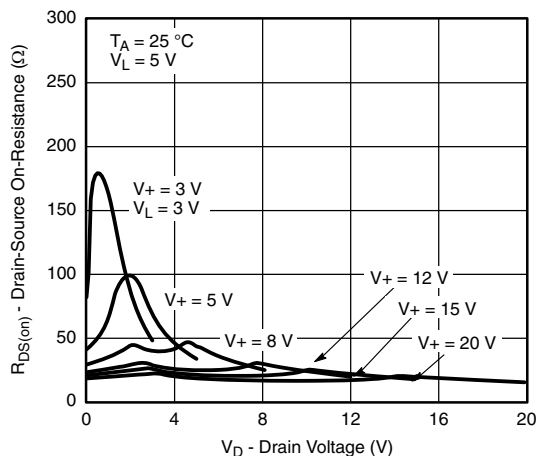
Notes

- Refer to PROCESS OPTION FLOWCHART.
- Room = 25 °C, full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform proper function.

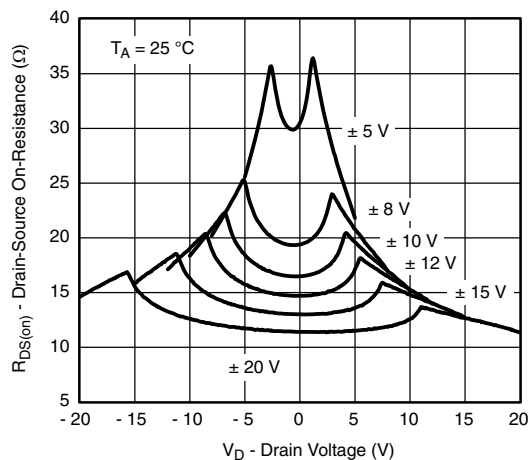
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



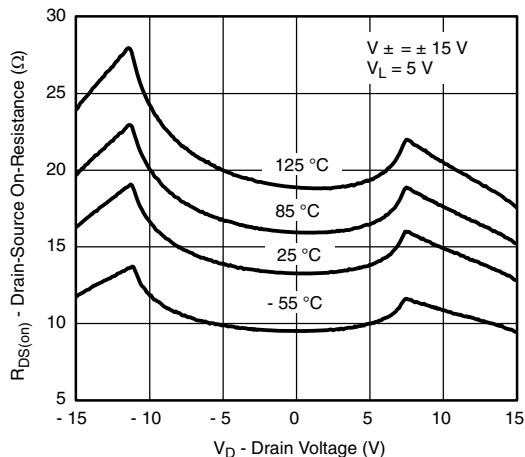
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



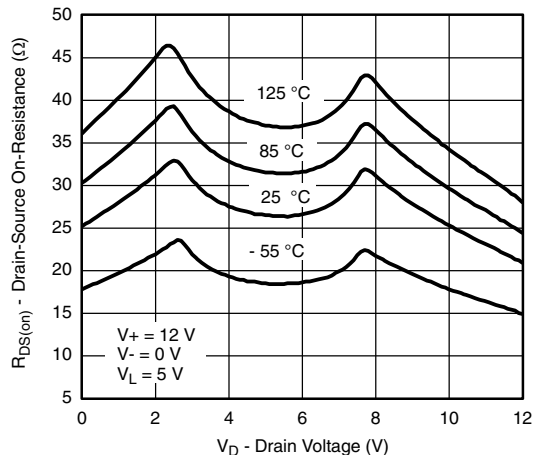
On-Resistance vs. V_D and Unipolar Power Supply Voltage



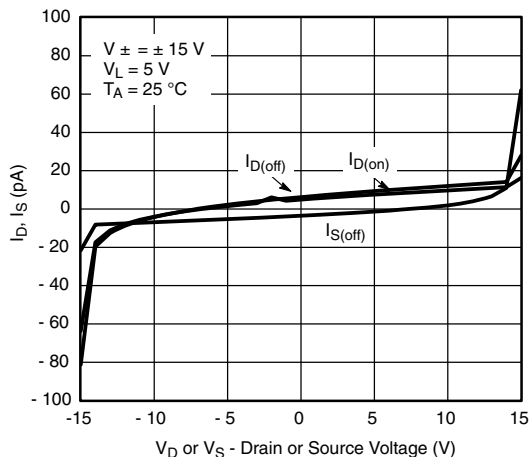
On-Resistance vs. V_D and Dual Supply Voltage



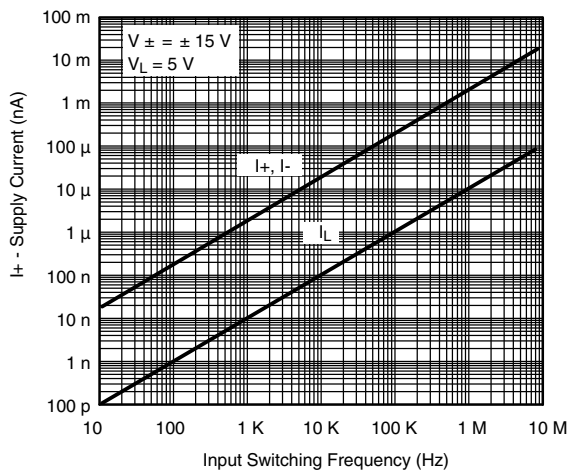
On-Resistance vs. V_D and Temperature



On-Resistance vs. V_D and Temperature



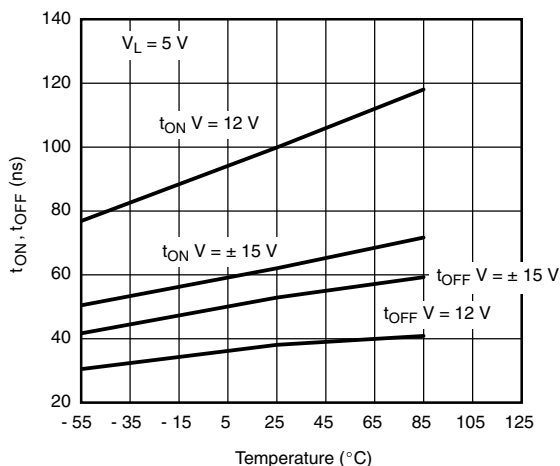
Leakage vs. Analog Voltage



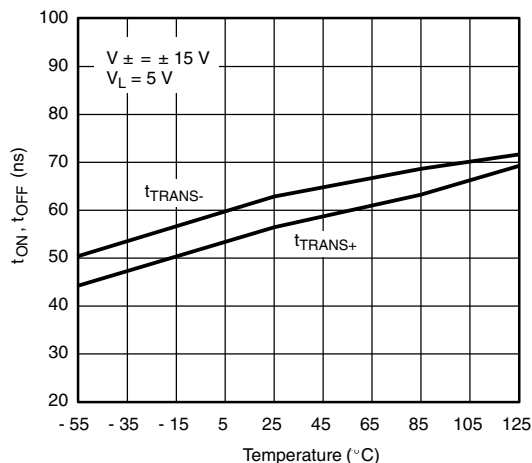
Supply current vs. Input Switching Frequency



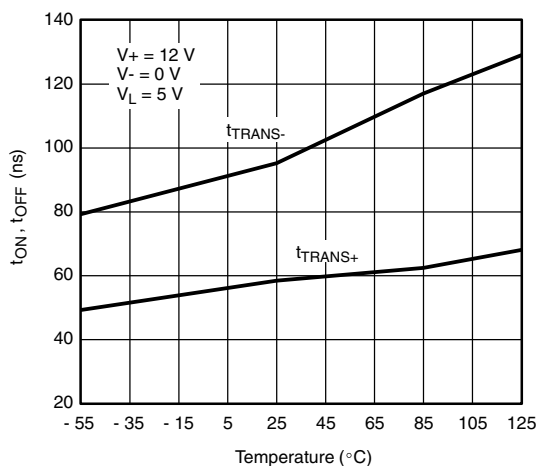
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



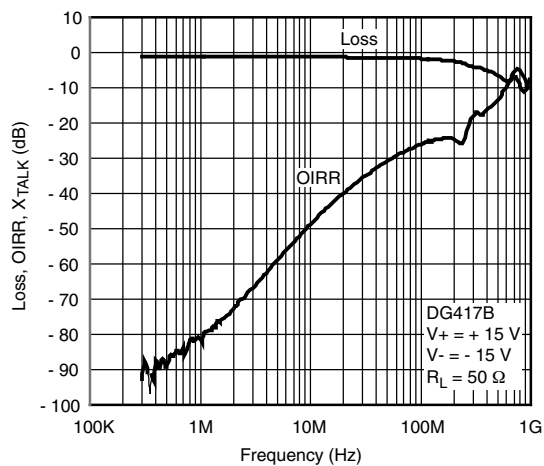
Switching Time vs. Temperature



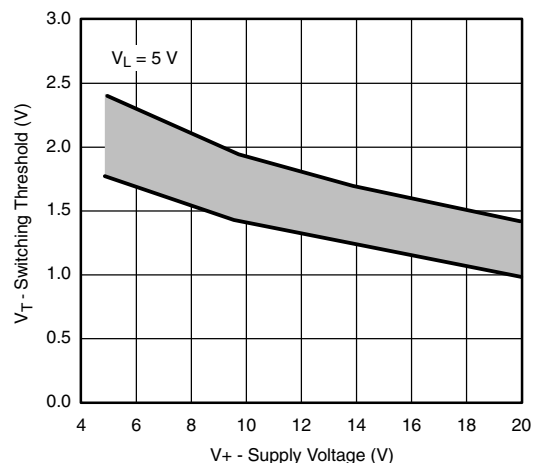
Transition Time vs. Temperature



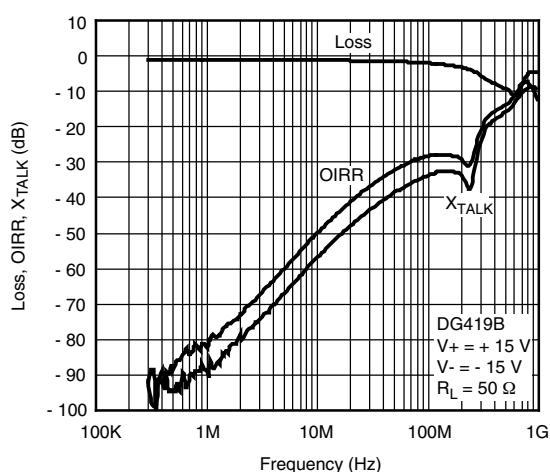
Transition Time vs. Temperature



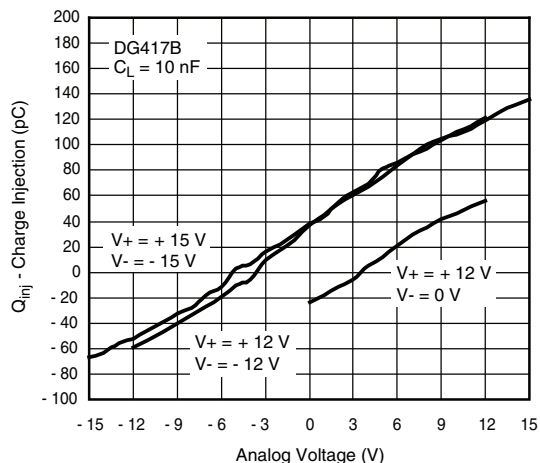
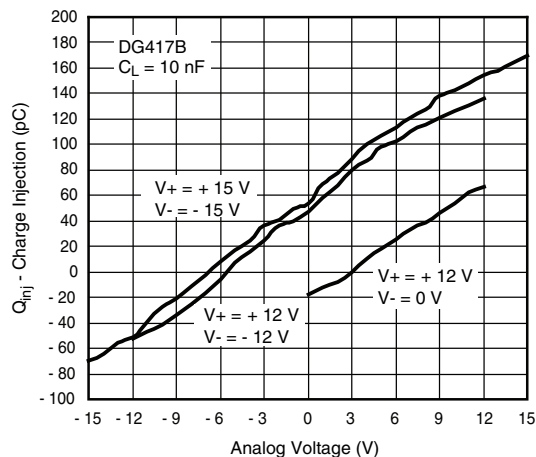
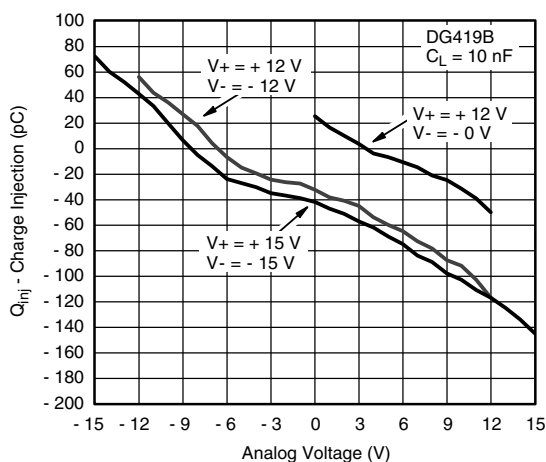
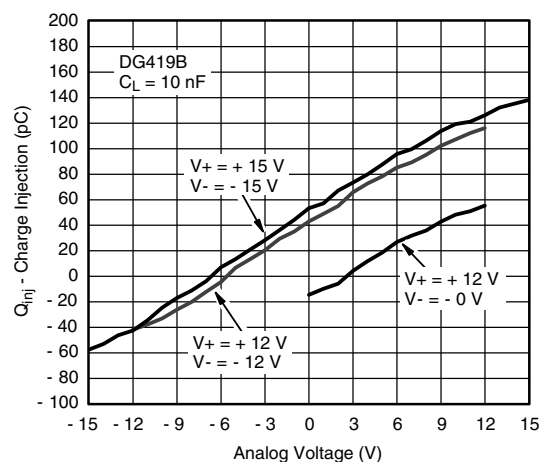
Insertion Loss, Off-Isolation Crosstalk vs. Frequency



Switching Threshold vs. Supply Voltage

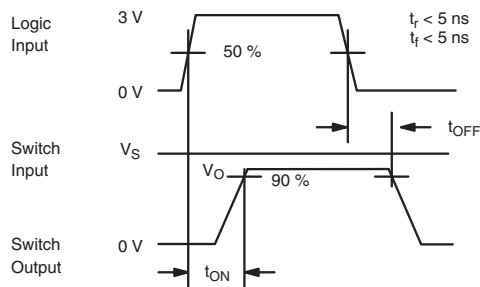
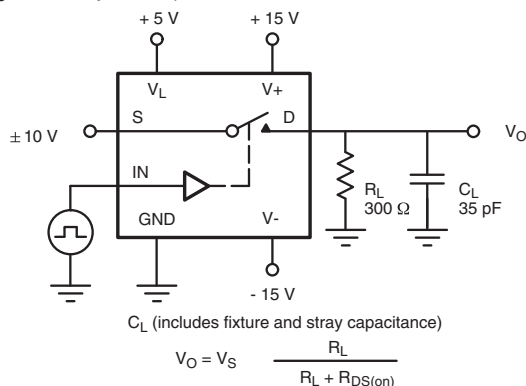


Insertion Loss, Off-Isolation Crosstalk vs. Frequency

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Charge Injection vs. Analog Voltage
(Measured at drain pin)

Charge Injection vs. Analog Voltage
(Measured at source pin)

Charge Injection vs. Analog Voltage
(Measured at drain pin)

Charge Injection vs. Analog Voltage
(Measured at source pin)

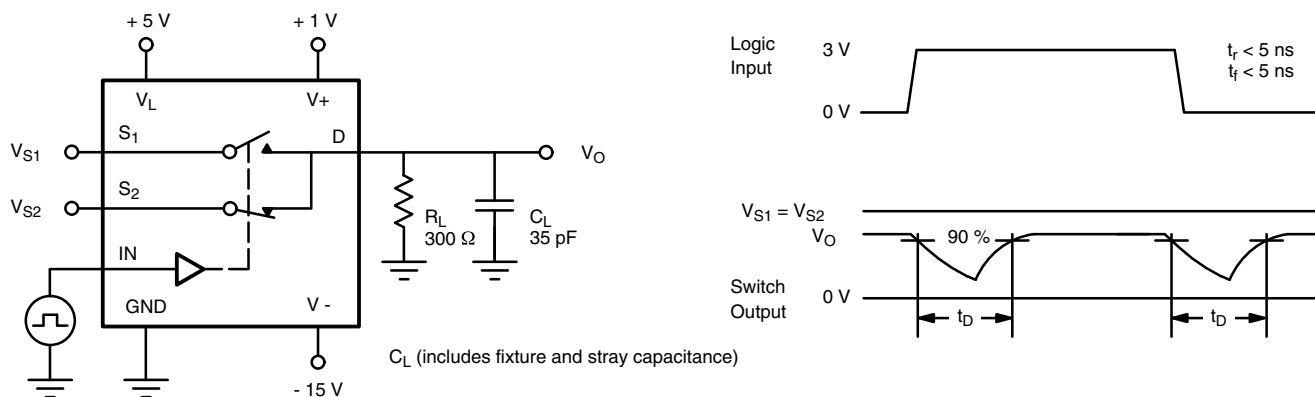
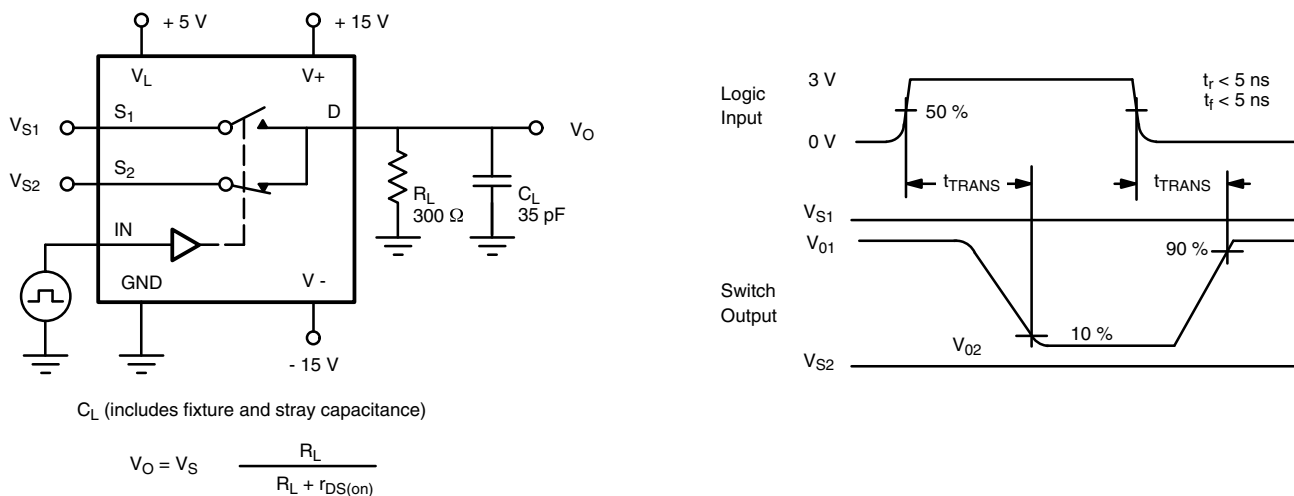
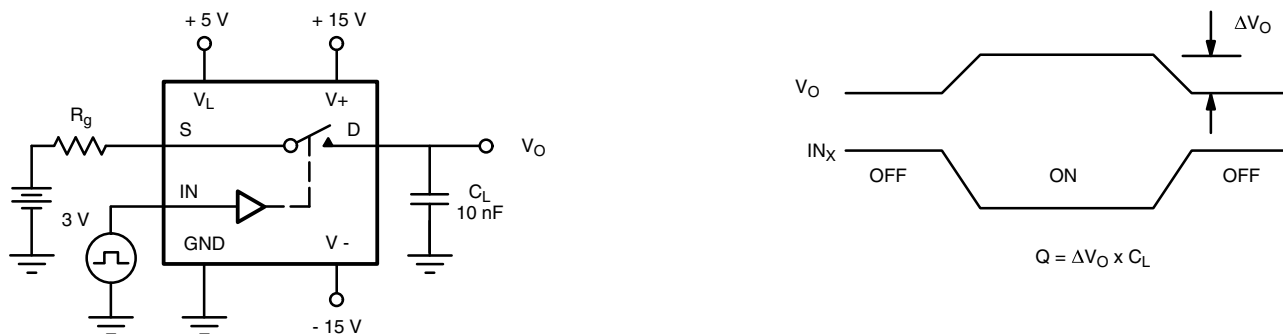
TEST CIRCUITS

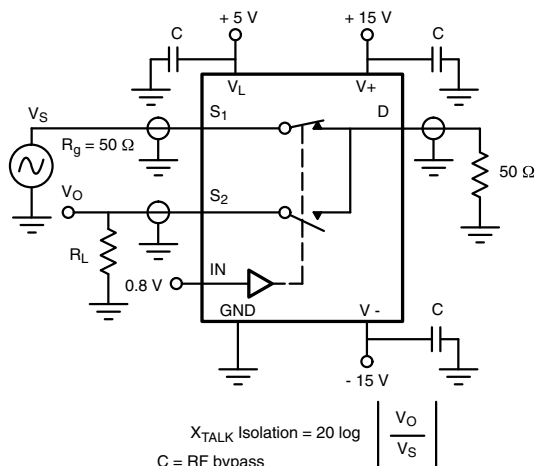
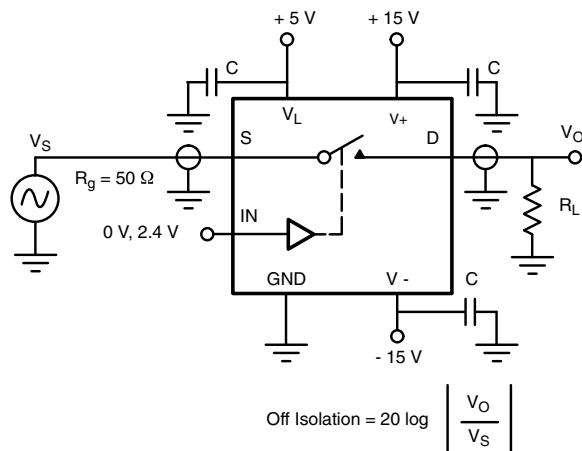
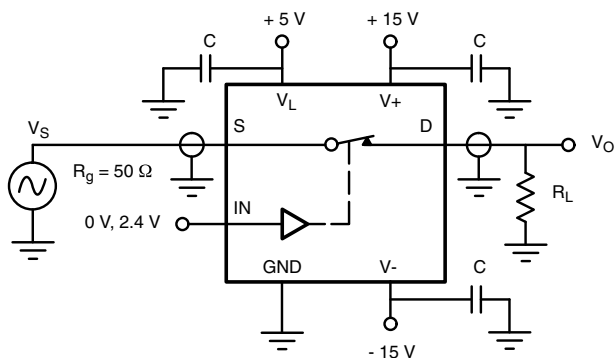
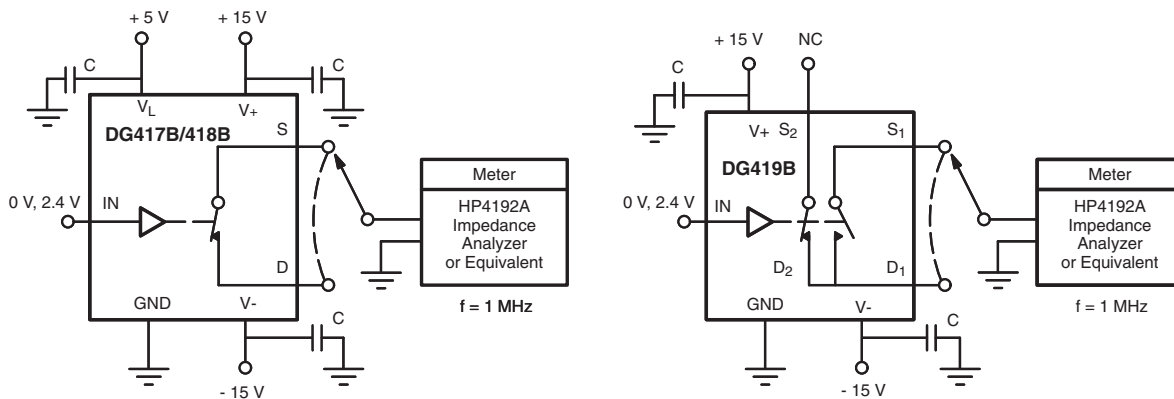
V_O is the steady state output with the switch on.



Note: Logic input waveform is inverted for switches that have the opposite logic sense.

Fig. 2 - Switching Time (DG417B, DG418B)

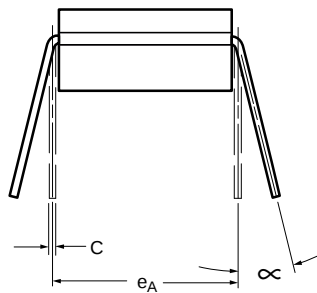
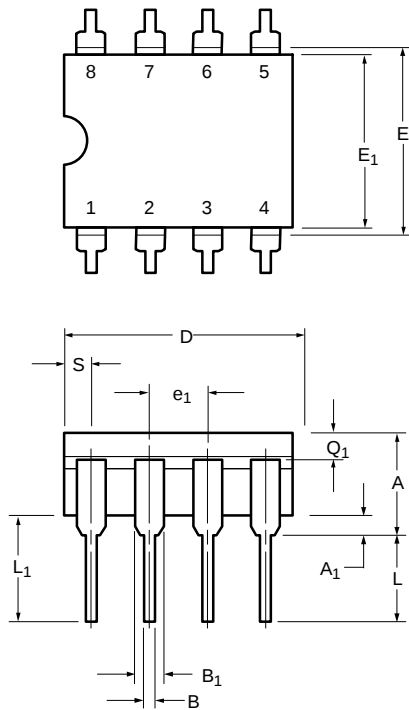
TEST CIRCUITS

Fig. 3 - Break-Before-Mak (DG419B)

Fig. 4 - Transition Time (DG419B)

Fig. 5 - Charge Injection

TEST CIRCUITS

Fig. 6 - Crosstalk

Fig. 7 - Off Isolation

Fig. 8 - Insertion Loss

Fig. 9 - Source-Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63275.



CERDIP: 8-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	4.06	5.08	0.160	0.200
A ₁	0.51	1.14	0.020	0.045
B	0.38	0.51	0.015	0.020
B ₁	1.14	1.65	0.045	0.065
C	0.20	0.30	0.008	0.012
D	9.40	10.16	0.370	0.400
E	7.62	8.26	0.300	0.325
E ₁	6.60	7.62	0.260	0.300
e ₁	2.54 BSC		0.100 BSC	
e _A	7.62 BSC		0.300 BSC	
L	3.18	3.81	0.125	0.150
L ₁	3.18	5.08	0.150	0.200
Q ₁	1.27	2.16	0.050	0.085
S	0.64	1.52	0.025	0.060
α	0°	15°	0°	15°

ECN: S-03946—Rev. C, 09-Jul-01
DWG: 5348



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.